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(54) **Title**: SEMICONDUCTOR DEVICE

[Fig. 1]

FIG. 1A

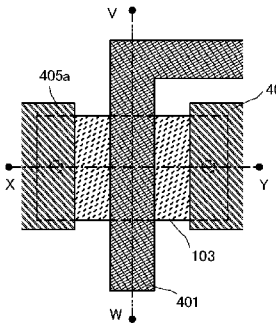


FIG. 1C

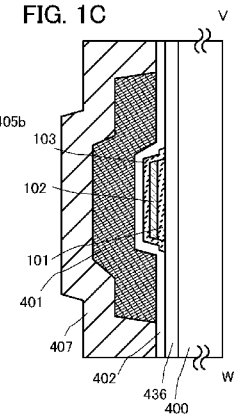
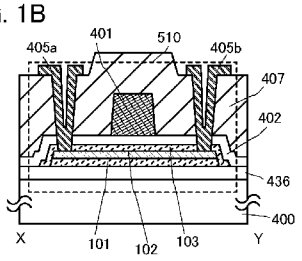


FIG. 1B



(57) **Abstract**: Stable electrical characteristics and high reliability are provided for a semiconductor device including an oxide semiconductor. In a transistor including an oxide semiconductor layer, a buffer layer containing a constituent similar to that of the oxide semiconductor layer is provided in contact with a top surface and a bottom surface of the oxide semiconductor layer. Such a transistor and a semiconductor device including the transistor are provided. As the buffer layer in contact with the oxide semiconductor layer, a film containing an oxide of one or more elements selected from aluminum, gallium, zirconium, hafnium, and a rare earth element can be used.

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